

December 2014

FCP380N60E / FCPF380N60E

N-Channel SuperFET[®] II Easy-Drive MOSFET 600 V, 10.2 A, 380 m Ω

Features

- 650 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 320 m Ω
- Ultra Low Gate Charge (Typ. Q_q = 34 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 97 pF)
- 100% Avalanche Tested
- · An Integrated Gate Resistor
- · RoHS Compliant

Applications

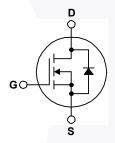
- · LCD / LED / PDP TV Lighting
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET easy-drive series offers slightly slower rise and fall times compared to the SuperFET II MOSFET series. Noted by the "E" part number suffix, this family helps manage EMI issues and allows for easier design implementation. For faster switching in applications where switching losses must be at an absolute minimum, please consider the SuperFET II MOSFET series.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCP380N60E	FCPF380N60E	Unit	
V _{DSS}	Drain to Source Voltage			600		V	
\/	Cata to Course Valtage	- DC		±	20	V	
V_{GSS}	Gate to Source Voltage	- AC	(f > 1 Hz)	±	30	V	
	Drain Current	- Continuous (T _C = 25°C)		10.2	10.2*	۸	
I _D Drain Current		- Continuous (T _C = 100°C)		6.4	6.4*	Α	
I _{DM}	Drain Current - Pulsed (Note 1)		30.6	30.6*	Α		
E _{AS}	Single Pulsed Avalanche Energy (Note 2		(Note 2)	211.6		mJ	
I _{AR}	Avalanche Current		(Note 1)	2.3		Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	1.06		mJ	
du/dt	MOSFET dv/dt			1	00	1//20	
dv/dt	Peak Diode Recovery dv/dt (Note		(Note 3)	3) 20		V/ns	
D	Device Dissipation	(T _C = 25°C)		106	31	W	
P _D Power Dissipation		- Derate Above 25°C	12	0.85	0.25	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°С		
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		5 Seconds	3	00	°С	

^{*}Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP380N60E	FCPF380N60E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.18	4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	*C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP380N60E	FCP380N60E	TO-220	Tube	N/A	N/A	50 units
FCPF380N60E	FCPF380N60E	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS} Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 25^{\circ}\text{C}$	600	-	-	V	
	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 150^{\circ}\text{C}$	650	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	-	0.67	-	V/°C
BV _{DS}	Drain to Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 10 A	_	700	-	V
1	Zoro Coto Voltago Proin Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	0.84	-	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2.5	-	3.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	-	0.32	0.38	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 5 \text{ A}$	-	10	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	1330	1770	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		945	1260	pF
C _{rss}	Reverse Transfer Capacitance			60	90	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	-	25	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 V \text{ to } 480 V, V_{GS} = 0 V$	-	97	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	Total Gate Charge at 10V $V_{DS} = 380 \text{ V}, I_D = 5 \text{ A},$		34	45	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	5.3	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	Gate to Drain "Miller" Charge (Note 4)		13	-	nC
ESR	Equivalent Series Resistance f = 1 MHz		-/	6	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		/ · -	17	44	ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 5 \text{ A},$	-	9	28	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R = 4.7 Ω	-	64	138	ns
t _f	Turn-Off Fall Time	(Note 4)	-	10	30	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	10.2	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	30.6	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 5 A		-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 5 A,	-	240	\ -	ns
Q _{rr}	Reverse Recovery Charge $dI_F/dt = 100 \text{ A}/\mu\text{s}$		-	3	-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I $_{AS}$ = 2.3 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. $I_{SD} \le 5.1$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}C$.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

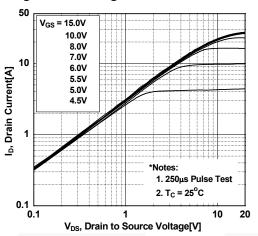


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

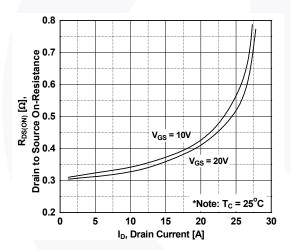


Figure 5. Capacitance Characteristics

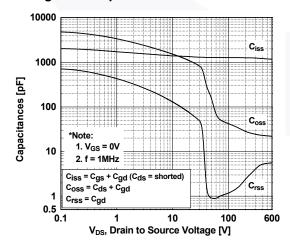


Figure 2. Transfer Characteristics

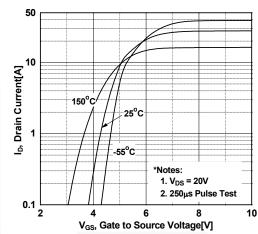


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

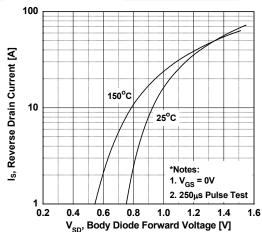
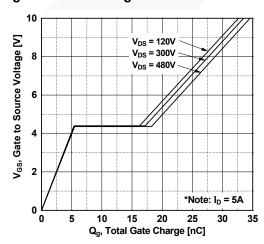


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

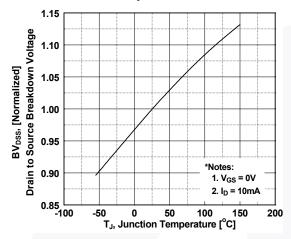


Figure 9. Maximum Safe Operating Area for FCP380N60E

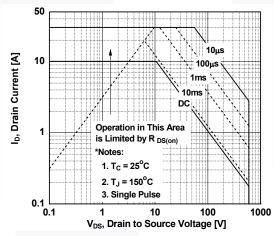


Figure 11. Maximum Drain Current vs. Case Temperature

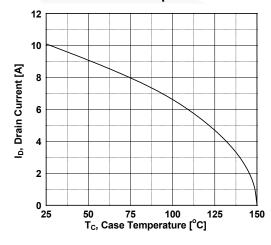


Figure 8. On-Resistance Variation vs. Temperature

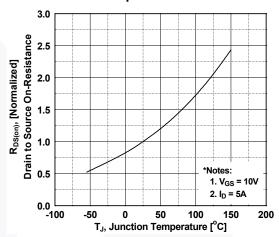


Figure 10. Maximum Safe Operating Area for FCPF380N60E

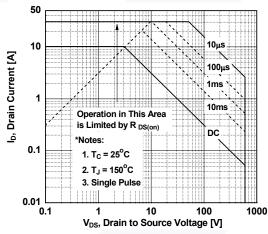
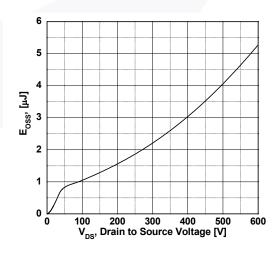


Figure 12. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve for FCP380N60E

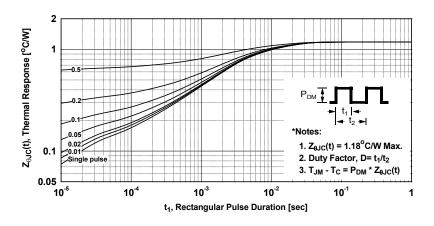
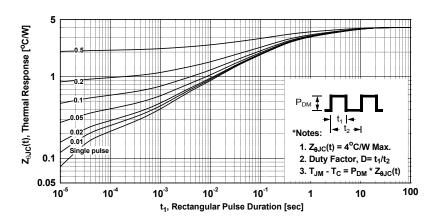


Figure 14. Transient Thermal Response Curve FOR FCPF380N60E



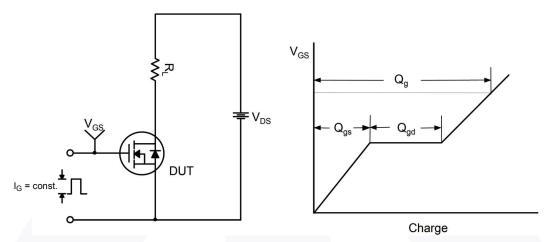


Figure 15. Gate Charge Test Circuit & Waveform

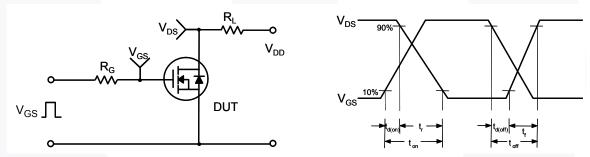


Figure 16. Resistive Switching Test Circuit & Waveforms

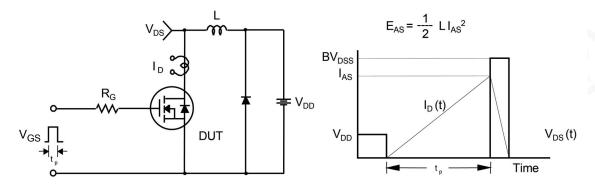


Figure 17. Unclamped Inductive Switching Test Circuit & Waveforms

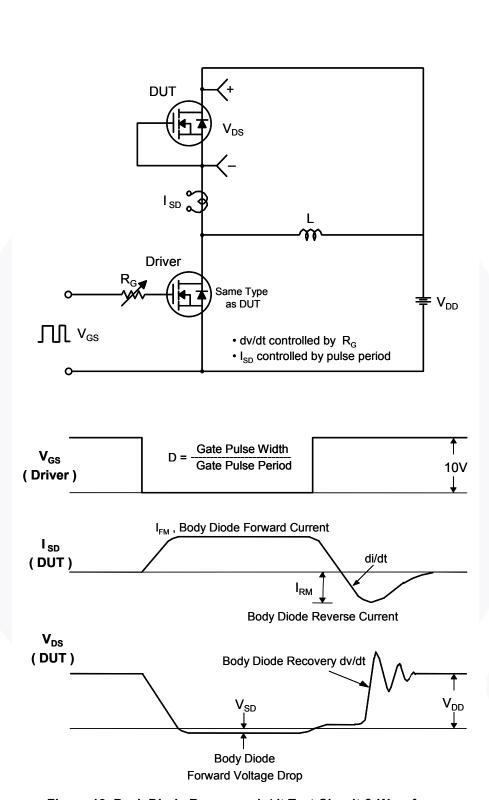
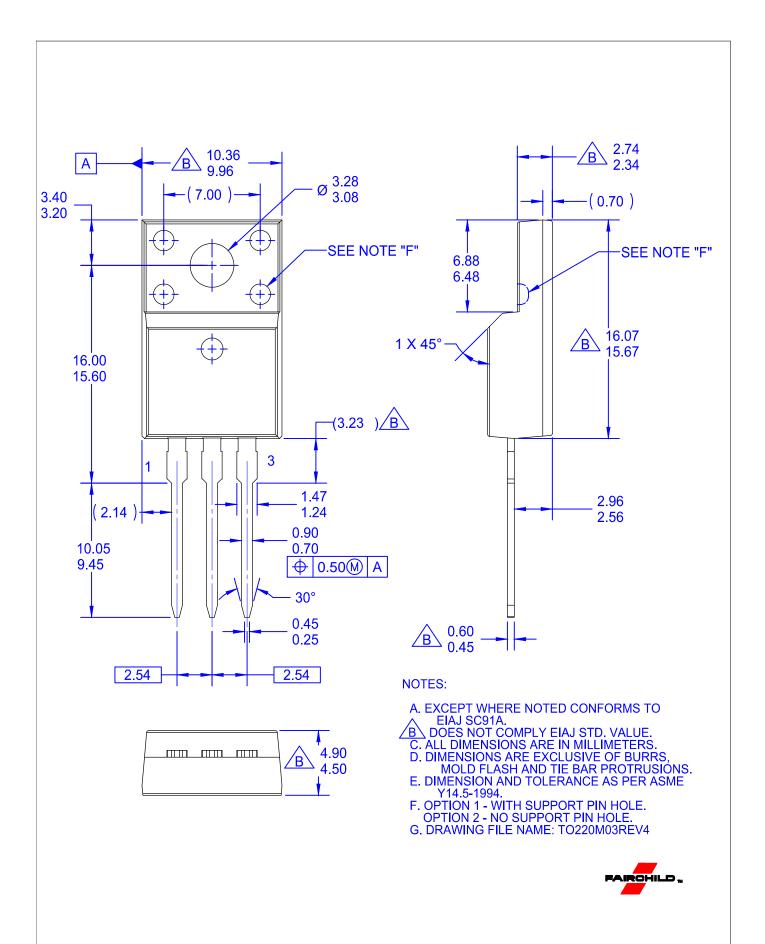


Figure 18. Peak Diode Recovery dv/dt Test Circuit & Waveforms









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Definition of Terms

Deminition of Terms		
Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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